

PRELIMINARY

※This datasheet is possibility of change.
Because this device is developing now.

ISC6046AU1

FOR GENERAL PURPOSE HIGH CURRENT DRIVE APPLICATION
SILICON NPN EPITAXIAL TYPE

DESCRIPTION

ISC6046AU1 is a silicon NPN epitaxial type transistor designed with high collector current, low $V_{CE(sat)}$.

FEATURE

- High collector current

$$I_{C(MAX)}=600mA$$

- Low collector to emitter saturation voltage

$$V_{CE(sat)} < 0.3V_{max} (I_C=150mA, I_B=15mA)$$

APPLICATION

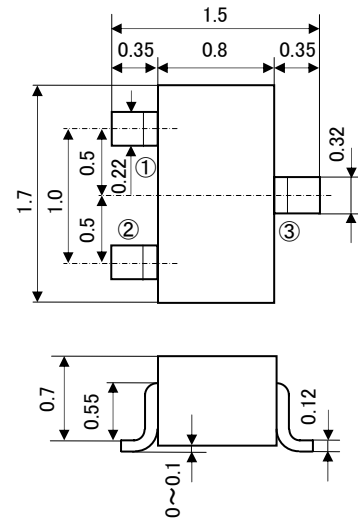
For switching application, small type motor drive application.

MAXIMUM RATINGS (Ta.=25°C)

記号	項目	定格値	単位
V_{CEO}	Collector to Emitter voltage	40	V
V_{CBO}	Collector to Base voltage	75	V
V_{EBO}	Emitter to Base voltage	6	V
I_C	Collector current	600	mA
P_C	Collector dissipation	150	mW
T_j	Junction temperature	+150	°C
T_{stg}	Storage temperature	-55~+150	°C

OUTLINE DRAWING

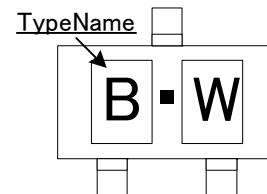
Unit: mm



TERMINAL CONNECTOR

①: BASE JEITA: SC-75A
②: EMITTER JEDEC: —
③: COLLECTOR

MARKING



ELECTRICAL CHARACTERISTICS (Ta.=25°C)

Symbol	Parameter	Test condition	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CEO}$	C to E break down voltage	$I_C=1mA, I_B=0$	40	—	—	V
$V_{(BR)CBO}$	C to B break down voltage	$I_C=10uA, I_E=0$	75	—	—	V
$V_{(BR)EBO}$	E to B break down voltage	$I_E=10uA, I_C=0$	6	—	—	V
I_{CBO}	Collector cut off current	$V_{CB}=60V, I_E=0$	—	—	100	nA
I_{EBO}	Emitter cut off current	$V_{EB}=3V, I_C=0$	—	—	100	nA
h_{FE}	DC forward current gain	$I_C=150mA, V_{CE}=10V$	100	—	300	—
$V_{CE(sat)}$	C to E saturation voltage	$I_C=150mA, I_B=15mA$	—	—	0.3	V
$V_{BE(sat)}$	B to E saturation voltage	$I_C=150mA, I_B=15mA$	0.6	—	1.2	V
f_T	Gain band width product	$I_E=-20mA, V_{CE}=20V, f=100MHz$	—	250	—	MHz
C_{ob}	Collector output capacitance	$V_{CB}=10V, f=1MHz$	—	—	8	pF

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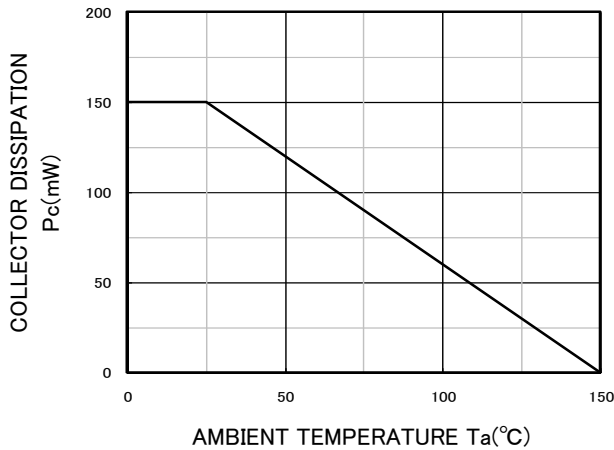
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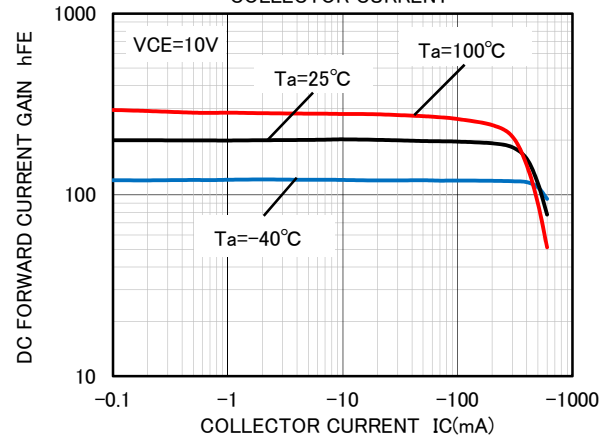
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TYPICAL CHARACTERISTICS

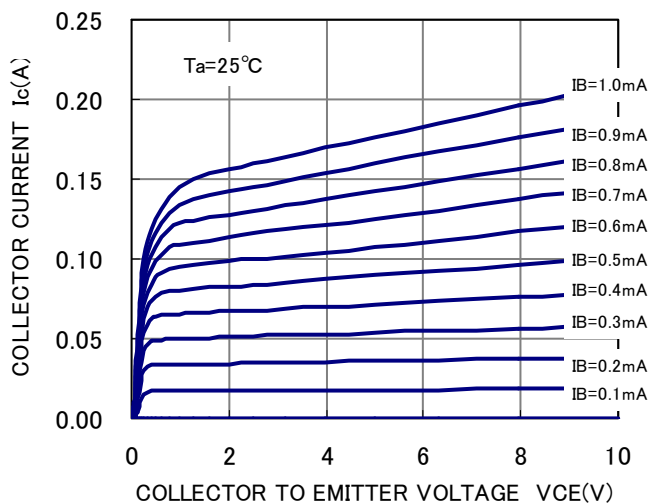
COLLECTOR DISSIPATION VS.
AMBIENT TEMPERATURE



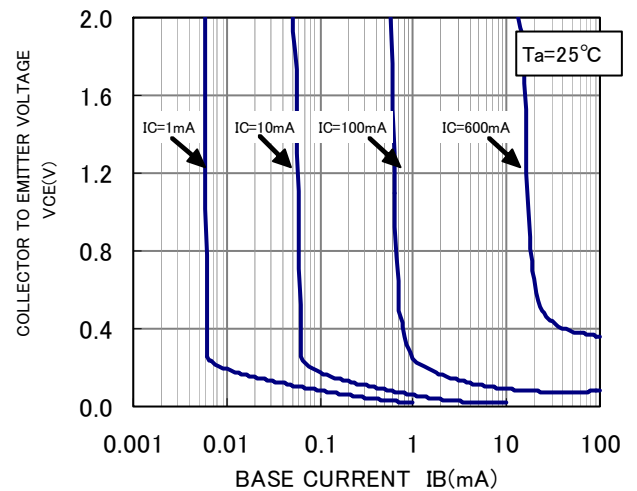
DC FORWARD CURRENT GAIN VS.
COLLECTOR CURRENT



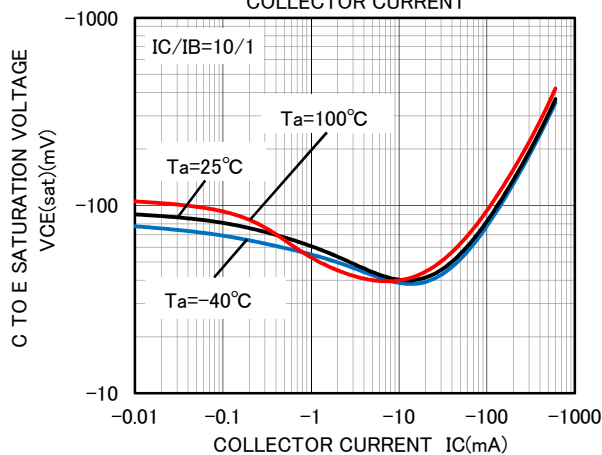
COMMON EMITTER OUTPUT



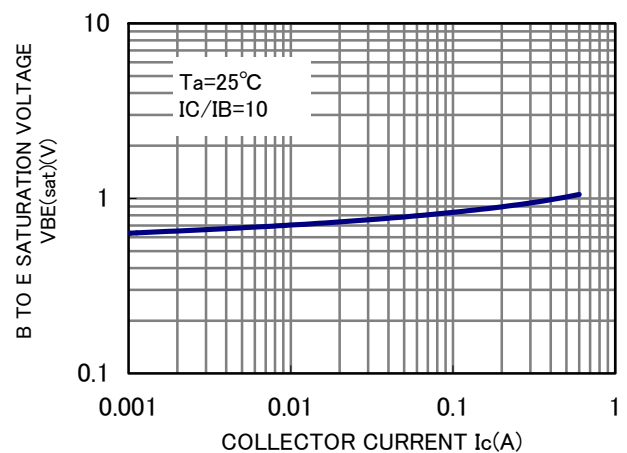
COLLECTOR TO EMITTER VOLTAGE VS.
BASE CURRENT



C TO E SATURATION VOLTAGE VS.
COLLECTOR CURRENT



B TO E SATURATION VOLTAGE VS.
COLLECTOR CURRENT



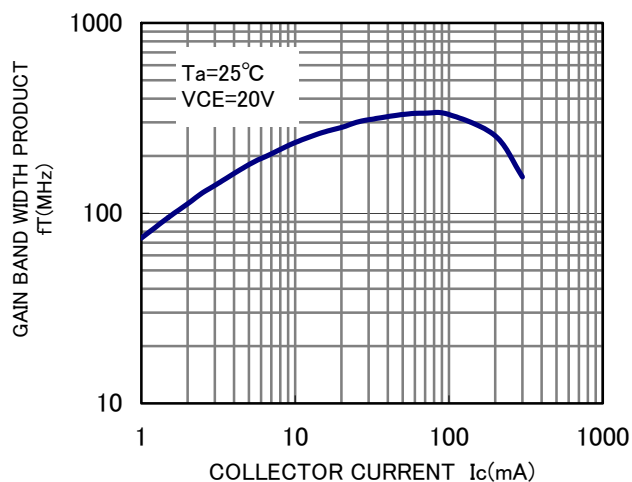
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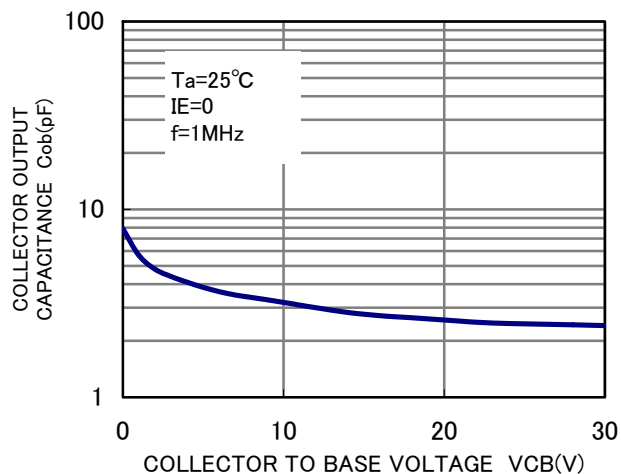
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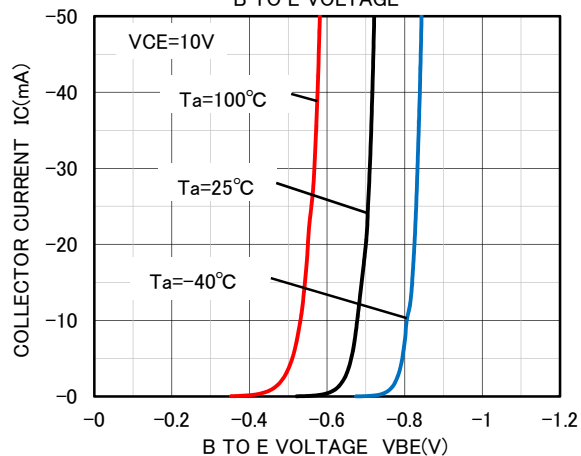
GAIN BAND WIDTH PRODUCT VS.
COLLECTOR CURRENT



COLLECTOR OUTPUT CAPACITANCE VS.
COLLECTOR TO BASE VOLTAGE



COLLECTOR CURRENT VS.
B TO E VOLTAGE





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